

Peak pulse voltage ($T_j=25$; non-repetitive,off-state;FIG.7)	V_{pp}	4.5	kV
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ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33$	- -	MAX.	5	mA
				10	
V_{GT}		ALL	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k$	ALL	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	- -	MAX.	15	mA
				20	
I_H	$I_T=500mA$		MAX.	10	mA
dV/dt	$V_D=540V$ Gate Open $T_j=125$		MIN.	40	V/ μs
$(dV/dt)_c$	$(dI/dt)_c=7.2A/ms$, $T_j=110$		MIN.	2	V/ μs

FIG.1: Maximum power dissipation versus RMS on-state current

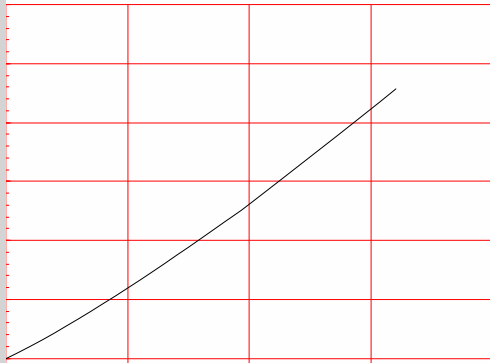



FIG.2: RMS on-state current versus case temperature

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